NSN 5961-01-641-5820

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Inclosure Material:
Ceramic and metal
Overall Length:
Between 0.895 inches and 0.906 inches
Semiconductor Material:
Silicon alloy
Current Rating Per Characteristic:
10.0 milliamperes emitter current, instantaneous
Power Rating Per Characteristic:
583.0 watts total power dissipation
Product Name:
Rf and microwave transistor
Special Features:
Designed for high power pulse iff, dme, and tacan; applications; 200 w (typ.) iff 1030 - 1090 mhz; 150 w (min.) dme 1025 - 1150 mhz;
140 w (typ.) tacan 960 - 1215 mhz; 8.2 db gain; refractory gold metallization; ballasting andlow thermal resistance for reliability and
ruggedness; 30: 1 load vswr capability at specified operating conditions;
Shelf Life:
N/a
Unit Of Measure:
-
Demilitarization:
No
Fiig:
A110a0